

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:29
L2	1	(semiconductor adj substrate) and ((film or layer) near (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:26
L3	26	(semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:26
L4	9	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:37
L5	13	(semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:30
L6	8	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:42
L7	1	(semiconductor adj substrate) and ((film or layer) near (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:39
L8	12	(semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:39

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L9	1	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and luminous and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:43
L10	3	(semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and luminous and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:43
S1	1	(film or layer) with (dry adj etch\$5) with (plasma adj emis\$4) with wavelength with endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:28
S2	2	(film or layer) same (dry adj etch\$5) same (plasma adj emis\$4) same wavelength same endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:28
S3	18	(film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:07
S4	50	(film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:12
S5	1	(film or layer) with (dry adj etch\$5) with (plasma adj (emis\$4 or discharg\$4)) with wavelength with endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:29
S6	4	(film or layer) same (dry adj etch\$5) same (plasma adj (emis\$4 or discharg\$4)) same wavelength same endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:29

## EAST Search History

S7	1763	(438/706).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 14:01
S8	1770	(438/706).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 14:01
S9	1	(film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:09
S10	0	438/706,5.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:10
S11	1	"438"/\$.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:10
S12	0	"257"/\$.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:10
S13	1	semiconductor and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:11
S14	1	semiconductor and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") or ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:11

## EAST Search History

S15	1	(film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") or ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:11
S16	6	(("5668019") or ("6514375") or ("5946082") or ("5450205") or ("5362356") or ("5322590")).PN.	USPAT	OR	OFF	2005/10/12 08:55
S17	1	(film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:12
S18	1	(film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint and ("SiCN") or ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:22
S19	1	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:23
S20	915	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:23
S21	19	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:38
S22	13	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:36

## EAST Search History

S23	1	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and (plasma adj (emis\$4 or discharg\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:35
S24	11	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:38
S25	6	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and plasma and (emiss\$4 or discharg\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:37
S26	19	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:39
S27	2	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:40
S28	1	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:24
S29	2	("5668019") or ("6703285").PN.	USPAT	OR	OFF	2005/10/12 08:55